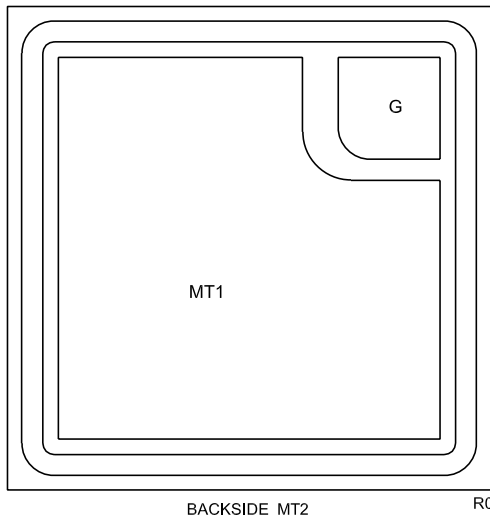


PROCESS DETAILS

Process	Glass Passivated Mesa
Die Size	165 x 165 MILS
Die Thickness	8.6 MILS ± 0.6 MILS
MT1 Bonding Pad Area	134 x 83 MILS
Gate Bonding Pad Area	35 x 35 MILS
Top Side Metalization	Al - 45,000Å
Back Side Metalization	Al/Mo/Ni/Ag - 32,000Å

GEOMETRY



GROSS DIE PER 4 INCH WAFER

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PRINCIPAL DEVICE TYPES

CQDD-25M Series
CQ220-25M Series
CQ220-25MFP Series

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R0 (20 -January 2006)